

## Isolation $\Sigma$ - $\Delta$ Modulator

### PRODUCT DESCRIPTION

The MS2401 is a second-order  $\Sigma$ - $\Delta$  modulator, an on-chip digital isolator, that converts analog input signals to high-speed 1-bit bitstream. The modulator continuously samples the input signal without requiring an external sample holding circuit. The analog signal input full range is  $\pm 320\text{mV}$  with a maximum data rate of 20 MHz for the converted digital stream. The VDD1 of MS2401 is powered by 5V power supply, and the VDD2 can be powered by 5V or 3V power supply.

The serial interface uses on-chip digital isolation to provide better performance. The device has a built-in reference voltage. The MS2401 is available in a 16-pin SOW package and the operating temperature range is  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ .



**SOW16**

### FEATURES

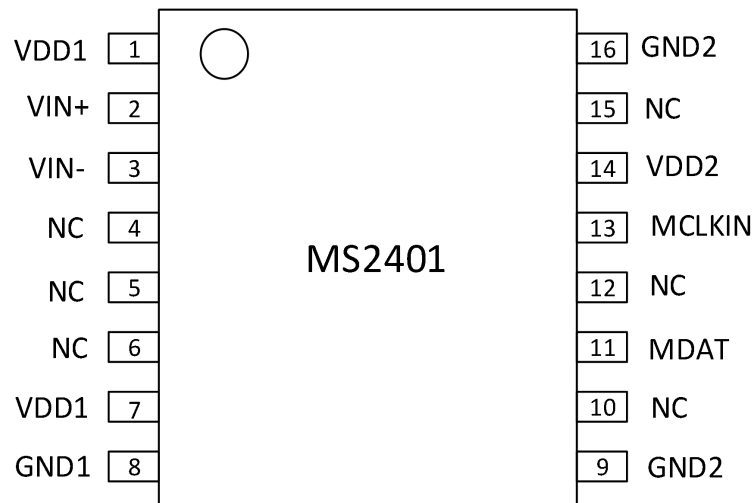
- 16 Bit No Missing Code
- Typical INL at 16 bits:  $\pm 2\text{LSB}$
- Offset Drift:  $1\mu\text{V}/^{\circ}\text{C}$
- Maximum External Clock Rate : 20MHz
- On-chip Digital Isolator
- Integrated Reference Voltage
- $\pm 250\text{mV}$  Analog Input Voltage (Full Range:  $\pm 320\text{mV}$ )
- Low Power Consumption Operation
- Operating Temperature Range:  $-40^{\circ}\text{C}$  to  $+ 125^{\circ}\text{C}$
- SOW16 Package
- Input-to-Output Momentary Withstand Voltage  
60s Duration: 5000Vrms

### APPLICATIONS

- AC Motor Control

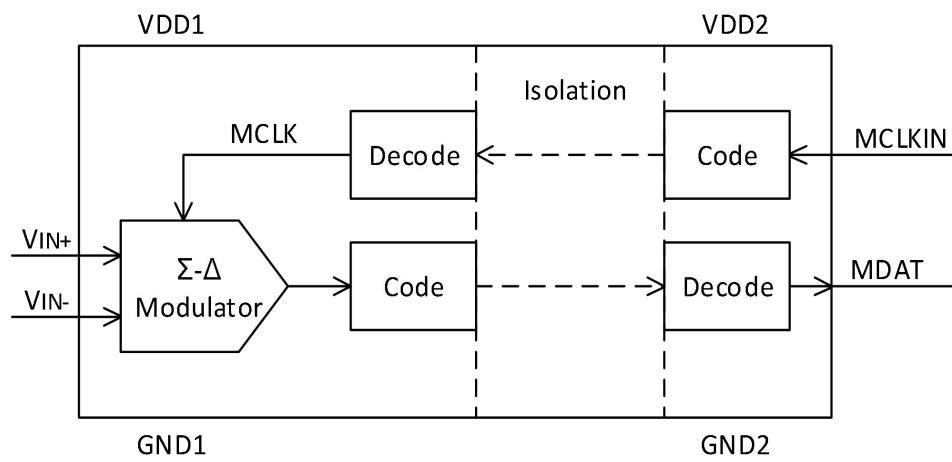
### PRODUCT SPECIFICATION

Part Number	Package	Marking
MS2401	SOW16	MS2401

**PIN CONFIGURATION**

**PIN DESCRIPTION**

Pin	Name	Type	Description
1,7	VDD1	I	Isolated Side Power Supply
2	VIN+	I	Positive Analog Input , the rated range is $\pm 250\text{mV}$
3	VIN-	I	Negative Analog Input , usually connected to GND1
4,5,6,10,12,15	NC	-	NC
8	GND1	I	Isolated Side Ground, this is the ground reference point for all circuits on the isolated side
9,16	GND2	I	Non-isolated Side Ground, this is the ground reference point for all circuits on the non-isolated side
11	MDAT	O	Serial Data Output, the output signal of the internal modulator is in the form of serial data stream, which is output from the pin to the outside. Each bit is displaced along the MCLKIN rising edge and is valid on the next MCLKIN rising edge
13	MCLKIN	I	Master Clock Input, maximum frequency is 20MHz, MDAT output stream is valid on MCLKIN rising edge
14	VDD2	I	Non-Isolated Side Power Supply

BLOCK DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

Any exceeding absolute maximum rating application causes permanent damage to device. Because long-time absolute operation state affects device reliability. Absolute ratings just conclude from a series of extreme tests. It doesn't represent chip can operate normally in these extreme conditions.

Parameter	Symbol	Range	Unit
Isolated Side Power Supply	VDD1-GND1	-0.3 ~ 6.5	V
Non-Isolated Side Power Supply	VDD2-GND2	-0.3 ~ 6.5	V
Analog Input Voltage to GND1	VIN-GND1	-0.3 ~ VDD1+0.3	V
Digital Input Voltage to GND2	VMCLKIN-GND2	-0.3 ~ VDD1+0.5	V
Output Voltage to GND2	VMDAT-GND2	-0.3 ~ VDD2+0.3	V
Input Current (Except Power Pin)	II	±10mA	mA
Storage Temperature Range	Tstg	-65 ~ +150	°C
Junction Temperature	TJ(MAX)	150	°C
Input to Output Resistance	RI-O	1012	Ω
Input to Output Capacitance	CI-O	1.7	pF
Lead-Free Temperature (10s)	TSOLDERING	260	°C
ESD(HBM)	ESD(HBM)	±3000	V

## RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Typ	Max	Unit
Isolated Side Power Supply	VDD1	4.5		5.5	V
Non-Isolated Side Power Supply	VDD2	3		5.5	V
Operating Temperature Range	TA	-40		+125	°C

**ELECTRICAL CHARACTERISTICS**

VDD1=5V, VDD2=3V to 5.5 V, VIN+ = -200mV to +200mV, and VIN-=0V (single-ended); TA=TMIN to TMAX, fMCLK=16 MHz maximum, tested with Sinc3 filter, 256 decimation rate, unless otherwise noted.

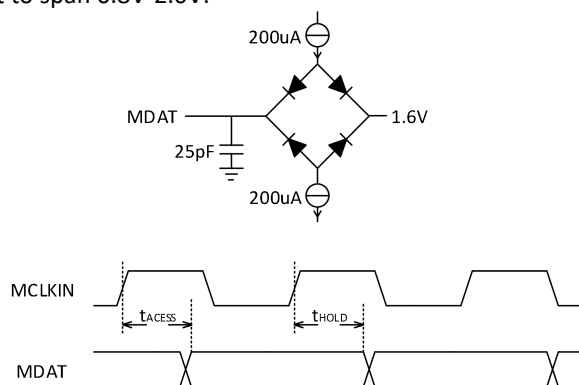
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Static Performance</b>						
Resolution		Filter output truncated to 16 bit	16			Bits
Integral Nonlinearity	INL	VIN+=±200mV, fMCLKIN=20MHz		±1.5	±7	LSB
		VIN+=±250mV, fMCLKIN=20MHz		±2.0	±13	
		VIN+=±200mV, fMCLKIN=20MHz		±1.5	±11	
		VIN+=±250mV, fMCLKIN=20MHz		±2	±46	
Differential Nonlinearity	DNL	VIN+= -250mV~250mV, fMCLKIN=20MHz			±0.9	LSB
Offset	VOS	VIN+= -250mV~250mV, fMCLKIN=20MHz		±0.25	±0.5	mV
Offset Drift VS. Temperature	TCVOS		1	3.5	μV/°C	
Offset Drift VS. VDD1	VCVOS		120		μV/V	
Gain Error	GERR		0.07	±1.5	mV	
Gain Error Drift VS. Temperature	TCGERR	VIN+= -250mV~250mV, fMCLKIN=20MHz		23		μV/°C
Gain Error Drift VS. VDD1	VCGERR			110		μV/V
<b>Analog Input</b>						
Input Voltage Range	VIN+ VIN-	Full Range ±320mV		±200	±250	mV
Dynamic Input Current	IIA	VIN+= 500mV, VIN-=0V fMCLKIN=20MHz		±13	±18	μA
		VIN+= 400mV, VIN-=0V fMCLKIN=20MHz		±10	±15	
		VIN+= 0V, VIN-=0V, fMCLKIN=20MHz		0.08		
DC Leakage Current	IIL			±0.01	±0.6	μA
Input Capacitance	CIA			10		pF

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Dynamic Specifications</b>						
Signal-to- (Noise +Distortion) Ratio	SINAD	VIN+=±200mV, fMCLKIN=5~20MHz, TA= -40°C~+85°C	76	82		dB
		VIN+=±250mV, fMCLKIN=5~20MHz, TA= -40°C~+85°C	71	82		
		VIN+=±200mV, fMCLKIN=5~20MHz, TA= -40°C~+125°C	72	82		
		VIN+=±250mV, fMCLKIN=5~20MHz, TA= -40°C~+125°C		82		
Signal-to-Noise Ratio	SNR	VIN+=±250mV, fMCLKIN=5~20MHz, TA= -40°C~+125°C	81	83		dB
		VIN+=±200mV, fMCLKIN=5~20MHz, TA= -40°C~+125°C	80	82		dB
Total Harmonic Distortion	THD	VIN+= -250mV~250mV, fMCLKIN=20MHz		-90		dB
Peak Harmonic or Spurious Noise	SFDR			-92		dB
Effective Number of Bits	ENOB		12.3	13.3		Bits
Isolation Transient Immunity	CMTI		25	30		kV/μs
<b>Logic Inputs</b>						
Input High Voltage	VIH		0.8×VDD2			V
Input Low Voltage	VIL		0.2×VDD2			V
Input Current	IIN				±0.5	μA
Input Capacitance	CID				10	pF
<b>Logic Outputs</b>						
Output High Voltage	VOH	IO= -200μA	VDD2-0.1			V
Output Low Voltage	VOL	IO= +200μA			0.4	V

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Power Requirements</b>						
Isolated Side Power Supply	VDD1		4.5		5.5	V
Non-isolated Side Power Supply	VDD2		3		5.5	V
Isolated side Power Supply Current	IDD1	VDD1=5.5V		14	16	mA
Non-isolated side Power Supply Current	IDD2	VDD2=5.5V		7	9	mA
		VDD2=3.3V		3	4	
Power Dissipation	PD	VDD1=VDD2=5.5V		93.5		mW
<b>Timing Specifications</b>						
Master Clock Input Frequency	fMCLKIN		5		20	MHz
Data Access Time after MCLK Rising Edge	tACCESS				25	ns
Data Hold Time after MCLK Rising Edge	tHOLD		15			ns
Clock Low to High Time		fMCLKIN ≤ 16MHz	40%		60%	
		16MHz < fMCLKIN ≤ 20MHz and VDD1=VDD2=5V±0.5%	48%		52%	
<b>Insulation and Safety Related Specifications</b>						
Input-to-Output Momentary Withstand Voltage	VISO	60s duration			5000	Vrms
Minimum External Air Gap	L(I01)	Measured from input terminals to output terminals, shortest distance through air			7.8	mm
Minimum External Tracking	L(I02)	Measured from input terminals to output terminals, shortest distance path along body			7.8	mm
Minimum Internal Gap	dISO	Insulation distance through insulation			0.018	mm

(1) All the voltages refer to their respective places.

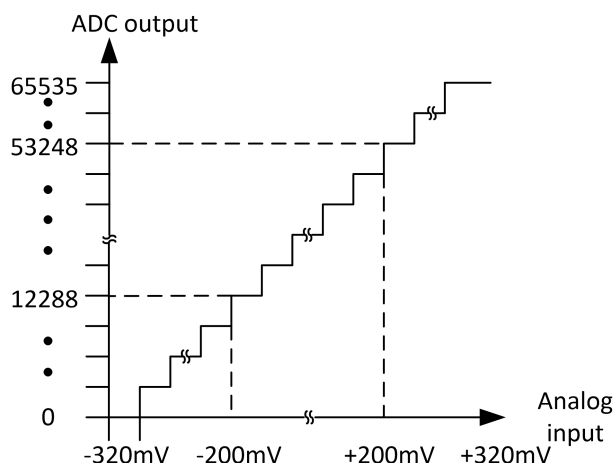
(2) The load circuit for the measurement sequence specification is shown below, and time is defined as the time required for the output to span 0.8V-2.0V.



## APPLICATIONS INFORMATION

### Analog Input

The MS2401 is able to convert the input signal to the output stream through a second-order modulator stage. In order to reconstruct the original information, it is required to digital filtering and decimation processing. And Sinc3 filter is recommended. Assuming an external clock frequency of 16 MHz, if the decimation rate is 256, the resulting 16-bit word rate is 62.5 kHz. In 16-bit output mode, the transfer function of the MS2401 is shown below.



### Digital Filter

The resolution and throughput of the system depend on the selected filter and the used decimation rate. The higher the decimation rate, the higher the accuracy of the system. However, there is a trade-off between accuracy and throughput, so the higher decimation rates yield solutions with lower throughput. It is recommended that the MS2401 be used with a Sinc3 filter.

### Grounding and Layout

It is recommended to connect 100nF power decoupling capacitors at VDD1 and VDD2 respectively. In applications with high common mode transients, it is important to ensure minimal circuit board coupling at both terminals of the isolation grid. In addition, when laying out the circuit board, it is important to consider that no coupling will occur and affect all pins on the side of a particular device. Decoupling capacitor should be as close to the power pin as possible. The series resistance of analog input should be minimized to avoid signal distortion.

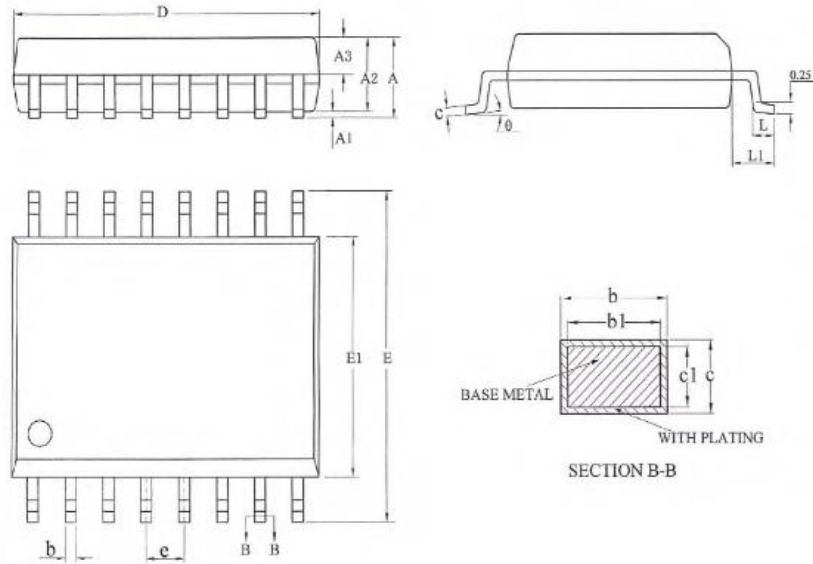
### Isolation Lifetime

All isolation structures are easy to break down under long-term use or high voltage. It should also be noted that the lifetime of the MS2401 varies with waveform type applied to the isolation structure. Integrated digital isolation structures decay at different rates, depending on whether the waveform is bipolar, unipolar, or DC.



**PACKAGE OUTLINE DIMENSIONS**

SOW16



Symbol	Millimeter		
	Min	Typ	Max
A	-	-	2.65
A1	0.10	-	0.30
A2	2.25	2.30	2.35
A3	0.97	1.02	1.07
b	0.35	-	0.44
b1	0.34	0.37	0.39
c	0.25	-	0.31
c1	0.24	0.25	0.26
D	10.10	10.30	10.50
E	10.26	10.41	10.60
E1	7.30	7.50	7.70
e	1.27BSC		
L	0.55	-	0.85
L1	1.40BSC		
θ	0	-	8°

**MARKING and PACKAGING SPECIFICATIONS**
**1. Marking Drawing Description**


Product Name : MS2401

Product Code : XXXXXXX

**2. Marking Drawing Demand**

Laser printing, contents in the middle, font type Arial.

**3. Packaging Specifications**

Device	Package	Piece/Reel	Reel/Box	Piece/Box	Box/Carton	Piece/Carton
MS2401	SOW16	1000	8	8000	1	8000

**STATEMENT**

- All Revision Rights of Datasheets Reserved for Ruimeng. Don't release additional notice.  
Customer should get latest version information and verify the integrity before placing order.
- When using Ruimeng products to design and produce, purchaser has the responsibility to observe safety standard and adopt corresponding precautions, in order to avoid personal injury and property loss caused by potential failure risk.
- The process of improving product is endless. And our company would sincerely provide more excellent product for customer.

**MOS CIRCUIT OPERATION PRECAUTIONS**

Static electricity can be generated in many places. The following precautions can be taken to effectively prevent the damage of MOS circuit caused by electrostatic discharge:

1. The operator shall ground through the anti-static wristband.
2. The equipment shell must be grounded.
3. The tools used in the assembly process must be grounded.
4. Must use conductor packaging or anti-static materials packaging or transportation.



+86-571-89966911



Rm701, No.9 Building, No. 1 WeiYe Road, Puyan Street, Binjiang District, Hangzhou, Zhejiang



[http:// www.relmon.com](http://www.relmon.com)